

ABSTRACT

A semiconductor nonvolatile storage circuit capable of stably storing and holding information by preventing pseudo-writing in storing/holding FETs is realized. The semiconductor nonvolatile circuit includes a first FET MNM1 forming a source-drain path between a ground potential GND and a bit line BL; a second FET MNM2 forming a source-drain path between the ground potential GND and a differential pair line BL<sub>-</sub>; a third FET MNM3 to open/close the connection between a drain terminal of the first FET MNM1 and the bit line BL; and a fourth FET MNM4 to open/close the connection between a drain terminal of the second FET MNM2 and the differential pair line BL<sub>-</sub>.